

**Amendments to the Specification:**

On page 5, please replace paragraph [0023] with the following amended paragraph.

[0023] In accordance with a first preferred embodiment as shown in FIG. 3, there is provided a flip chip package. The flip chip package mainly comprises a lead frame 31, a chip 32 and a plurality of bumps 33. The bumps 33 include first bumps 331 and second bumps 332. The lead frame 31, for example a leadless leadframe, has a die paddle 311 and a plurality of leads 312 surrounding the die paddle 311 as shown in FIG. 4. Therein the die paddle 311 has a plurality of first concavities 311a and one of the leads 312 has a second concavity 312a. The first concavity 311a and the second concavity 312a can be formed by the method of punching and half-etching. Besides, the chip 32 has an active surface 321, a first bonding pads [[322]] 321a on the active surface 321, a second bonding pads [[324]] 321b on the active surface, a plurality of first bumps [[321a]] 331 formed on the first bonding pads [[322]] 321a and a plurality of second bumps [[321b]] 332 formed on the second bonding pads [[324]] 321b. Moreover, the active surface 321 of the chip 32 faces the lead frame 31 and electrically connects to the lead frame 31 via the bumps 32 by the method of flip chip bonding technique.

On page 6, please replace paragraph [0028] with the following amended paragraph.

[0028] Besides, the first bumps 331 can be conductive bumps, e.g. gold bumps and solder bumps. Thus the die paddle 311 can be electrically connected to the chip 32 via the first bumps 331 to provide the chip 31 another grounding and thermal dissipation paths to enhance the operation performance of the chip [[31]] 32.